

APR 11 2003

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**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

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 APR 12 2003  
 PATENT & TRADEMARK OFFICE  
 U.S. DEPARTMENT OF COMMERCE

Complete if Known

Application Number	09/943134
Filing Date	August 30, 2001
First Named Inventor	Forbes, Leonard
Group Art Unit	2818
Examiner Name	Ho, Tu-Tu
Sheet 1 of 3	Attorney Docket No: 1303.020US1

**US PATENT DOCUMENTS**

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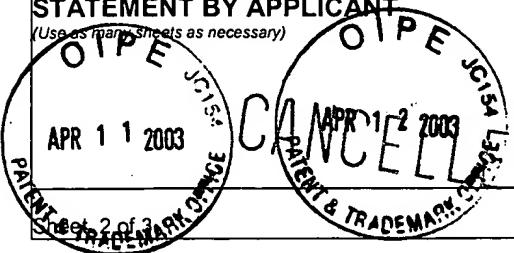
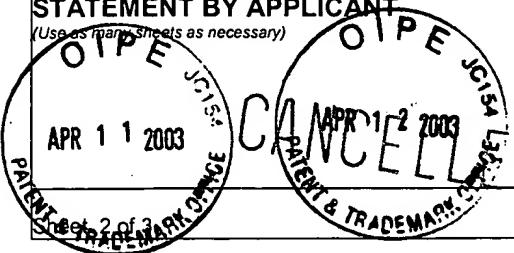
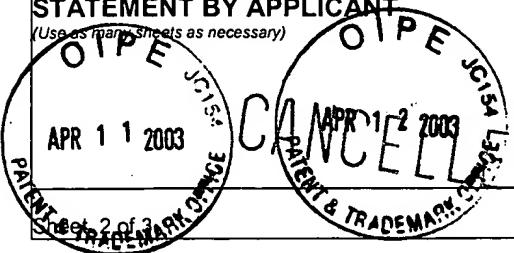
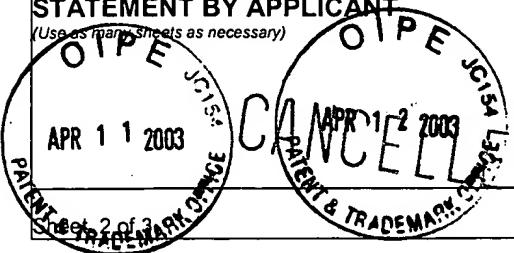
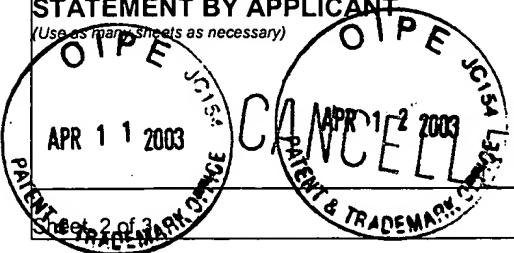
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Substitute Disclosure Statement Form (PTO-1449)

\* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached

Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (Use as many sheets as necessary)		Complete if Known	
		<b>Application Number</b>	09/943134
		<b>Filing Date</b>	August 30, 2001
		<b>First Named Inventor</b>	Forbes, Leonard
		<b>Group Art Unit</b>	2818
		<b>Examiner Name</b>	Ho, Tu-Tu
Attorney Docket No: 1303.020US1			

### FOREIGN PATENT DOCUMENTS

Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T <sup>2</sup>
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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS						
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Sheet 3 of 3

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APR 17 2003  
C A N C E L L E D  
U. S. PATENT & TRADEMARK OFFICE

Attorney Docket No: 1303.020US1

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EXAMINER

Tu-Tu Ho

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